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Automotive High Performance Logic Gates

NLV18SGxx, NLV28WGxx

The NLG18SGxx are automotive−grade High Performance single CMOS logic gates. The NLV28WGxx are automotive−grade high Performance Dual CMOS logic gates.

Features

- High Speed: t_{PD} = 3.7 ns (Typ) at V_{CC} = 3.0 V, C_L = 15 pF
- Low Power Dissipation: I_{CC} = 0.5 μA (Max) at T_A = 25°C
- High Noise Immunity
- Balanced Propagation Delays ($t_{PLH} = t_{PHL}$)
- 3.6 V Overvoltage−Tolerant Input and Output Pins
- AEC Grade 1−Compliant: −40°C to +125°C
- Tiny SC−88A and SC−88 Packages
- AEC−Q100 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and RoHS Compliant

FUNCTION LIST

xx	Function
00	2−Input NAND
02	2−Input NOR
04	Inverter
06	Open−Drain Inverter
07	Open−Drain Buffer
08	2−Input AND
14	Schmitt−Trigger Inverter
17	Schmitt−Trigger Buffer
32	2−Input OR
34	Buffer
86	2−Input XOR
125	Tri−State Buffer
126	Tri−State Buffer
U04	Unbuffered Inverter

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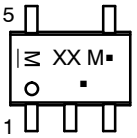
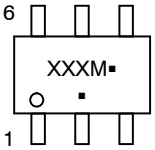
SC−88A
DF SUFFIX
CASE 419A



1

SC−88
CASE 419B



MARKING DIAGRAMS

XX = Device Code
M = Date Code*
▪ = Pb−Free Package

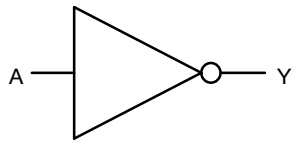
(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

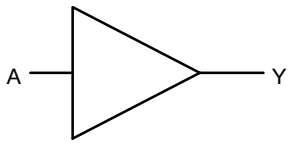
See detailed ordering and shipping information on page 11 of this data sheet.

Functions and Function Tables – Buffers and Inverters



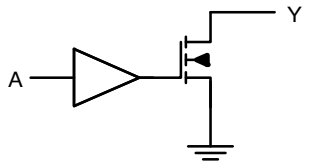
04 – Inverter
U04 – Unbuffered Inverter

A	Y
0	1
1	0



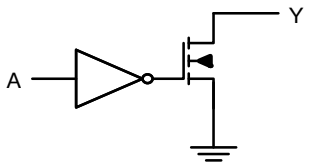
34 – Buffer

A	Y
0	0
1	1



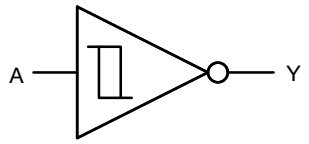
06 – Open–Drain Inverter

A	Y
0	Hi–Z
1	0



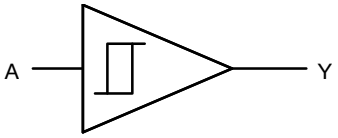
07 – Open–Drain Buffer

A	Y
0	0
1	Hi–Z



14 – Schmitt–Trigger Inverter

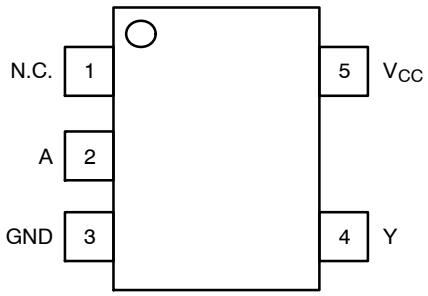
A	Y
0	1
1	0



17 – Schmitt–Trigger Buffer

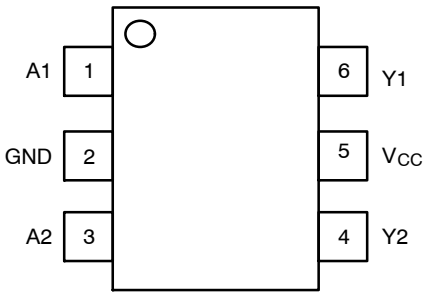
A	Y
0	0
1	1

Pin Assignment



Pinout (Single Buffers and Inverters)

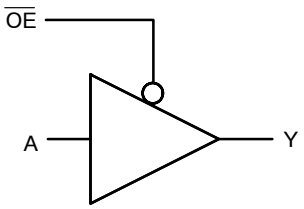
Pin	Name	Description
1	N.C.	No Connection
2	A	Input
3	GND	Ground
4	Y	Output
5	V_{CC}	Supply



Pinout (Dual Buffers and Inverters)

Pin	Name	Description
1	A1	Input 1
2	GND	Ground
3	A2	Input 2
4	Y	Output 2
5	V_{CC}	Supply
6	Y1	Output 1

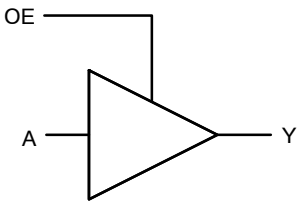
Functions and Function Tables – Tri−State Buffers and Bus Drivers



125 − Tri−State Buffer

$\overline{OE}$	A	Y
0	0	0
0	1	1
1	X	Hi−Z

X = Don't Care

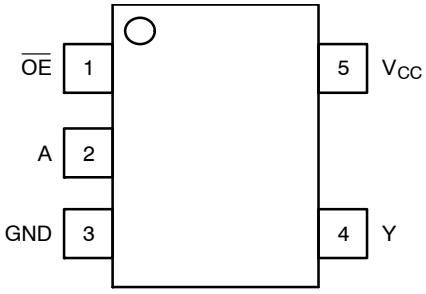


126 − Tri−State Buffer

OE	A	Y
0	X	Hi−Z
1	0	0
1	1	1

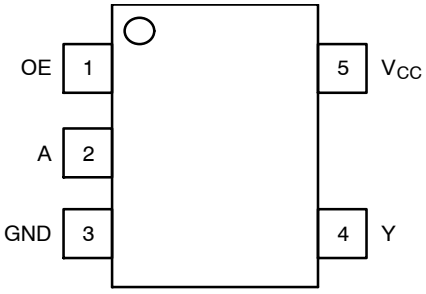
X = Don't Care

Pin Assignments



Pinout (125)

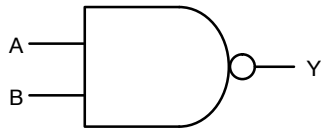
Pin	Name	Description
1	$\overline{OE}$	Enable (Active−Low)
2	A	Input
3	GND	Ground
4	Y	Output
5	V_{CC}	Supply



Pinout (126)

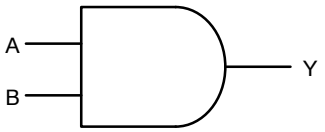
Pin	Name	Description
1	OE	Enable (Active−High)
2	A	Input
3	GND	Ground
4	Y	Output
5	V_{CC}	Supply

Functions and Function Tables – Gates



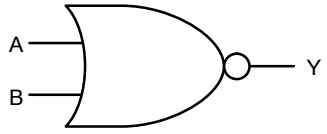
00 – NAND

A	B	Y
0	0	1
0	1	1
1	0	1
1	1	0



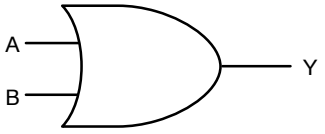
08 – AND

A	B	Y
0	0	0
0	1	0
1	0	0
1	1	1



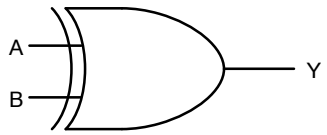
02 – NOR

A	B	Y
0	0	1
0	1	0
1	0	0
1	1	0



32 – OR

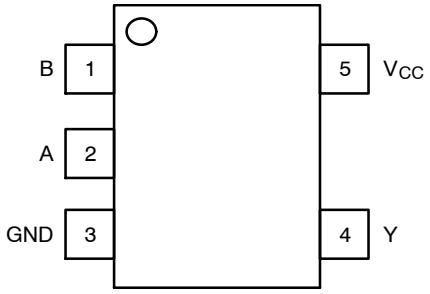
A	B	Y
0	0	0
0	1	1
1	0	1
1	1	1



86 – XOR

A	B	Y
0	0	0
0	1	1
1	0	1
1	1	0

Pin Assignment



Pinout (Gates)

Pin	Name	Description
1	B	Input
2	A	Input
3	GND	Ground
4	Y	Output
5	V_{CC}	Supply

Table 1. MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +4.3	V
V_{IN}	DC Input Voltage		−0.5 to +4.3	V
V_{OUT}	DC Output Voltage (U04)		−0.5 to V_{CC}+0.5	V
	DC Output Voltage (Other functions)	Active−Mode (High or Low State) Tri−State Mode (Note 1) Power−Down Mode (V_{CC} = 0 V)	−0.5 to V_{CC}+0.5 −0.5 to +4.3 −0.5 to +4.3	
I_{IK}	DC Input Diode Current		−20	mA
I_{OK}	DC Output Diode Current		−20	mA
I_{OUT}	DC Output Source/Sink Current		±20	mA
I_{CC} or I_{GND}	DC Supply Current Per Supply Pin or Ground Pin		±20	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
T_J	Junction Temperature Under Bias		+150	°C
θ_{JA}	Thermal Resistance (Note 2)		377	°C/W
P_D	Power Dissipation in Still Air		332	mW
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	2000 1000	V
$I_{LATCHUP}$	Latchup Performance (Note 4)		±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri−stated.
2. Measured with minimum pad spacing on an FR4 board, using 10 mm−by−1 inch, 20 ounce copper trace with no air flow per JESD51−7.
3. HBM tested to EIA / JESD22−A114−A. CDM tested to JESD22−C101−A. JEDEC recommends that ESD qualification to EIA/JESD22−A115A (Machine Model) be discontinued.
4. Tested to EIA/JESD78 Class II.

Table 2. RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	Positive DC Supply Voltage		0.9	3.6	V
V_{IN}	Digital Input Voltage		0	3.6	V
V_{OUT}	DC Output Voltage (U04)		0	V_{CC}	V
	DC Output Voltage (Other functions)	Active−Mode (High or Low State) Tri−State Mode (Note 1) Power−Down Mode (V_{CC} = 0 V)	0 0 0	V_{CC} 3.6 3.6	
T_A	Operating Free−Air Temperature		−40	+125	°C
t_r, t_f	Input Transition Rise or Fall Rate				ns/V
	Functions 14 and 17		0	No Limit	
	All Other Functions	V_{CC} = 3.3 V ± 0.3 V	0	10	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

Table 3. DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	V_{CC} (V)	T_A = 25°C			T_A = −40°C to +125°C		Unit
				Min	Typ	Max	Min	Max	
FUNCTIONS 14 and 17									
V_{T+}	Positive−Going Threshold		0.9	–	0.6	–	–	–	V
			1.1	–	0.73	0.95	–	0.95	
			1.4	–	0.92	1.16	–	1.16	
			1.65	–	1.07	1.3	–	1.3	
			2.3	–	1.44	1.73	–	1.73	
			3.0	–	1.82	2.24	–	2.24	
V_{T-}	Negative−Going Threshold		0.9	–	0.34	–	–	–	V
			1.1	0.15	0.4	–	0.15	–	
			1.4	0.3	0.52	–	0.3	–	
			1.65	0.35	0.62	–	0.35	–	
			2.3	0.55	0.92	–	0.55	–	
			3.0	0.95	1.24	–	0.95	–	
V_H	Hysteresis Voltage		0.9	–	0.27	–	–	–	V
			1.1	0.2	0.33	0.8	0.2	0.8	
			1.4	0.25	0.5	0.86	0.25	0.86	
			1.65	0.3	0.5	0.9	0.3	0.9	
			2.3	0.4	0.5	1.05	0.4	1.05	
			3.0	0.49	0.65	1.1	0.49	1.1	
FUNCTION U04 (Under Development)									
V_{IH}	High−Level Input Voltage		0.9	–	TBD	–	–	–	V
			1.1 to 1.3	TBD	–	–	TBD	–	
			1.4 to 1.6	TBD	–	–	TBD	–	
			1.65 to 1.95	TBD	–	–	TBD	–	
			2.3 to 2.7	TBD	–	–	TBD	–	
			3.0 to 3.6	TBD	–	–	TBD	–	
V_{IL}	Low−Level Input Voltage		0.9	–	TBD	–	–	–	V
			1.1 to 1.3	–	–	TBD	–	TBD	
			1.4 to 1.6	–	–	TBD	–	TBD	
			1.65 to 1.95	–	–	TBD	–	TBD	
			2.3 to 2.7	–	–	TBD	–	TBD	
ALL OTHER FUNCTIONS									
V_{IH}	High−Level Input Voltage		0.9	V_{CC}	–	–	V_{CC}	–	V
			1.1 to 1.3	0.7 x V_{CC}	–	–	0.7 x V_{CC}	–	
			1.4 to 1.6	0.65 x V_{CC}	–	–	0.65 x V_{CC}	–	
			1.65 to 1.95	0.65 x V_{CC}	–	–	0.65 x V_{CC}	–	
			2.3 to 2.7	1.7	–	–	1.7	–	
			3.0 to 3.6	2.0	–	–	2.0	–	

Table 3. DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	V_{CC} (V)	T_A = 25°C			T_A = −40°C to +125°C		Unit
				Min	Typ	Max	Min	Max	
ALL OTHER FUNCTIONS									
V_{IL}	Low−Level Input Voltage		0.9	–	–	GND	–	GND	V
			1.1 to 1.3	–	–	0.3 x V_{CC}	–	0.3 x V_{CC}	
			1.4 to 1.6	–	–	0.35 x V_{CC}	–	0.35 x V_{CC}	
			1.65 to 1.95	–	–	0.35 x V_{CC}	–	0.35 x V_{CC}	
			2.3 to 2.7	–	–	0.7	–	0.7	
			3.0 to 3.6	–	–	0.8	–	0.8	
ALL FUNCTIONS									
V_{OH}	High−Level Output Voltage(Note 5)	V_{IN} = V_{IH} or V_{IL}							V
		I_{OH} = −20 μA	0.9	–	0.75	–	–	–	
		I_{OH} = −0.3 mA	1.1 o 1.3	0.75 x V_{CC}	–	–	0.75 x V_{CC}	–	
		I_{OH} = −1.7 mA	1.4 to 1.6	0.75 x V_{CC}	–	–	0.75 x V_{CC}	–	
		I_{OH} = −3.0 mA	1.65 to 1.95	V_{CC} − 0.45	–	–	V_{CC} − 0.45	–	
		I_{OH} = −4.0 mA	2.3 to 2.7	2.0	–	–	2.0	–	
		I_{OH} = −8.0 mA	3.0 to 3.6	2.48	–	–	2.48	–	
V_{OL}	Low−Level Output Voltage	V_{IN} = V_{IH} or V_{IL}							V
		I_{OL} = 20 μA	0.9	–	0.1	–	–	–	
		I_{OL} = 0.3 mA	1.1 o 1.3	–	–	0.25 x V_{CC}	–	0.25 x V_{CC}	
		I_{OL} = 1.7 mA	1.4 to 1.6	–	–	0.25 x V_{CC}	–	0.25 x V_{CC}	
		I_{OL} = 3.0 mA	1.65 to 1.95	–	–	0.45	–	0.45	
		I_{OL} = 4.0 mA	2.3 to 2.7	–	–	0.4	–	0.4	
		I_{OL} = 8.0 mA	2.7 to 3.6	–	–	0.4	–	0.4	
I_{IN}	Input Leakage Current	V_{IN} = 3.6 V or GND	0.9 to 3.6	–	–	±0.1	–	±1.0	μA
I_{OZ}	3−State Output Leakage Current	V_{IN} = 0 V to 3.6 V; V_{OUT} = 0 V to 3.6 V	0.9 to 3.6	–	–	1.0	–	10.0	μA
I_{OFF}	Power Off Leakage Current (function U04 only)	V_{IN} = 0 V to 3.6 V	0	–	–	1.0	–	10.0	μA
	Power Off Leakage Current (except function U04)	V_{IN} = 0 V to 3.6 V; V_{OUT} = 0 V to 3.6 V	0	–	–	1.0	–	10.0	
I_{CC}	Quiescent Supply Current	V_{IN} = V_{CC} or GND	3.6	–	–	1.0	–	10.0	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. The V_{OH} parameter does not apply to devices with open−drain output, NLV18SG06 and NLV18SG07.

Table 4. AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Condition	V_{CC} (V)	T_A = 25°C			T_A = −40°C to +125°C		Unit
				Min	Typ	Max	Min	Max	
t_{PLH}, t_{PHL}	Propagation Delay, (A or B) to Y (Figures 1 and 2)	C_L = 10 pF, R_L = 1 MΩ	0.9	–	27.3	–	–	–	ns
			1.1 to 1.3	–	13.0	22.6	–	35.9	
			1.4 to 1.6	–	7.5	10.5	–	11.3	
			1.65 to 1.95	–	6.0	7.8	–	8.2	
			2.3 to 2.7	–	4.3	5.4	–	5.8	
			3.0 to 3.6	–	3.5	4.4	–	4.6	
		C_L = 15 pF, R_L = 1 MΩ	0.9	–	29.5	–	–	–	
			1.1 to 1.3	–	14.3	25.1	–	41.6	
			1.4 to 1.6	–	8.0	11.5	–	12.6	
			1.65 to 1.95	–	6.3	8.4	–	8.7	
			2.3 to 2.7	–	4.6	5.7	–	6.1	
			3.0 to 3.6	–	3.7	4.6	–	5.0	
		C_L = 30 pF, R_L = 1 MΩ	0.9	–	40.5	–	–	–	
			1.1 to 1.3	–	19.6	35.7	–	58.1	
			1.4 to 1.6	–	10.7	15.8	–	17.6	
			1.65 to 1.95	–	7.8	10.7	–	11.7	
			2.3 to 2.7	–	5.4	6.9	–	8.1	
			3.0 to 3.6	–	4.3	5.2	–	6.1	
t_{PZH}, t_{PZL}	Output Enable Time, (A or OE) to Y (Figures 1 and 2)	C_L = 10 pF; R_L = 100 kΩ	0.9	–	11.0	–	–	–	ns
		R_L = 5 kΩ	1.1 to 1.3	–	8.4	10.9	–	13.0	
		R_L = 5 kΩ	1.4 to 1.6	–	5.3	7.8	–	8.3	
		R_L = 5 kΩ	1.65 to 1.95	–	3.9	5.5	–	5.9	
		R_L = 5 kΩ	2.3 to 2.7	–	2.5	3.5	–	3.8	
		R_L = 5 kΩ	3.0 to 3.6	–	2.1	2.7	–	3.0	
		C_L = 15 pF; R_L = 100 kΩ	0.9	–	12.0	–	–	–	
		R_L = 5 kΩ	1.1 to 1.3	–	9.0	11.7	–	13.8	
		R_L = 5 kΩ	1.4 to 1.6	–	5.9	8.9	–	11.0	
		R_L = 5 kΩ	1.65 to 1.95	–	4.4	6.3	–	6.5	
		R_L = 5 kΩ	2.3 to 2.7	–	2.9	3.9	–	4.2	
		R_L = 5 kΩ	3.0 to 3.6	–	2.3	3.0	–	3.3	
		C_L = 30 pF; R_L = 100 kΩ	0.9	–	13.0	–	–	–	
		R_L = 5 kΩ	1.1 to 1.3	–	10.0	13.1	–	15.2	
		R_L = 5 kΩ	1.4 to 1.6	–	8.3	12.2	–	13.7	
		R_L = 5 kΩ	1.65 to 1.95	–	6.1	8.6	–	9.7	
		R_L = 5 kΩ	2.3 to 2.7	–	3.8	5.0	–	5.5	
		R_L = 5 kΩ	3.0 to 3.6	–	2.9	3.8	–	4.2	

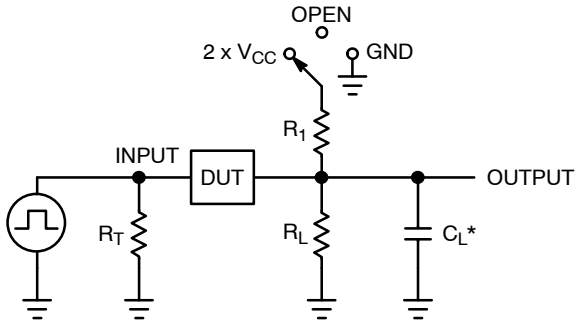
Table 4. AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Condition	V_{CC} (V)	T_A = 25°C			T_A = −40°C to +125°C		Unit
				Min	Typ	Max	Min	Max	
t_{PHZ}, t_{PLZ}	Output Disable Time, (A or OE) to Y (Figures 1 and 2)	C_L = 10 pF; R_L = 100 kΩ	0.9	–	100.4	–	–	–	ns
		R_L = 5 kΩ	1.1 to 1.3	–	9.1	14.4	–	22.4	
		R_L = 5 kΩ	1.4 to 1.6	–	7.1	9.1	–	10.4	
		R_L = 5 kΩ	1.65 to 1.95	–	6.5	8.3	–	9.0	
		R_L = 5 kΩ	2.3 to 2.7	–	5.8	7.3	–	8.8	
		R_L = 5 kΩ	3.0 to 3.6	–	5.4	6.9	–	7.6	
		C_L = 15 pF; R_L = 100 kΩ	0.9	–	122.2	–	–	–	
		R_L = 5 kΩ	1.1 to 1.3	–	9.8	15.3	–	25.1	
		R_L = 5 kΩ	1.4 to 1.6	–	7.8	9.8	–	11.3	
		R_L = 5 kΩ	1.65 to 1.95	–	7.2	9.2	–	10.6	
		R_L = 5 kΩ	2.3 to 2.7	–	7.0	8.2	–	10.3	
		R_L = 5 kΩ	3.0 to 3.6	–	6.6	7.7	–	9.5	
		C_L = 30 pF; R_L = 100 kΩ	0.9	–	217.1	–	–	–	
		R_L = 5 kΩ	1.1 to 1.3	–	13.2	19.6	–	31.9	
		R_L = 5 kΩ	1.4 to 1.6	–	12.2	13.5	–	14.9	
		R_L = 5 kΩ	1.65 to 1.95	–	11.4	12.7	–	13.9	
		R_L = 5 kΩ	2.3 to 2.7	–	11.3	12.2	–	13.5	
		R_L = 5 kΩ	3.0 to 3.6	–	10.2	11.5	–	12.9	

Table 5. CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Units
C_{IN}	Input Capacitance	V_{CC} = 3.6 V	3.0	pF
C_{PD}	Power Dissipation Capacitance (Note 6)	10 MHz, V_{CC} = 3.3 V, V_{IN} = 0 V or V_{CC}	4.0	pF

6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no−load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.



C_L includes probe and jig capacitance
R_T is Z_{OUT} of pulse generator (typically 50 Ω)
f = 1 MHz

Figure 1. Test Circuit

Test	Switch Position
t_{PLH} / t_{PHL}	Open
t_{PLZ} / t_{PZL}	2 x V_{CC}
t_{PHZ} / t_{PZH}	GND

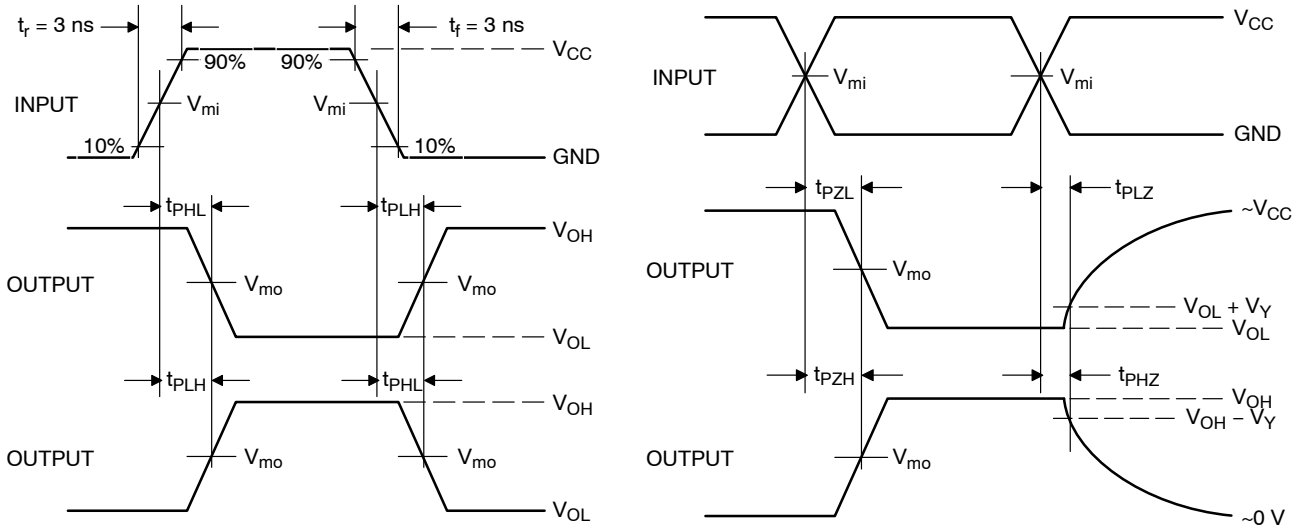


Figure 2. Switching Waveforms

V_{CC}, V	V_{mi}, V	V_{mo}, V	V_Y, V
0.9	V_{CC}/2	V_{CC}/2	0.1
1.1 to 1.3	V_{CC}/2	V_{CC}/2	0.1
1.4 to 1.6	V_{CC}/2	V_{CC}/2	0.1
1.65 to 1.95	V_{CC}/2	V_{CC}/2	0.15
2.3 to 2.7	V_{CC}/2	V_{CC}/2	0.15
3.0 to 3.6	1.5	1.5	0.3

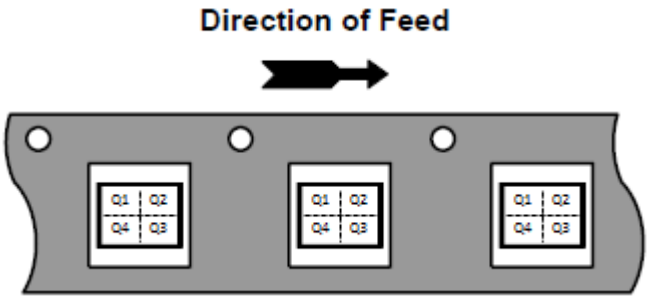
ORDERING INFORMATION

Device	Package	Marking	Pin 1 Orientation (See below)	Shipping†
NLV18SG08DFT2G	SC−88A	AT	Q4	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

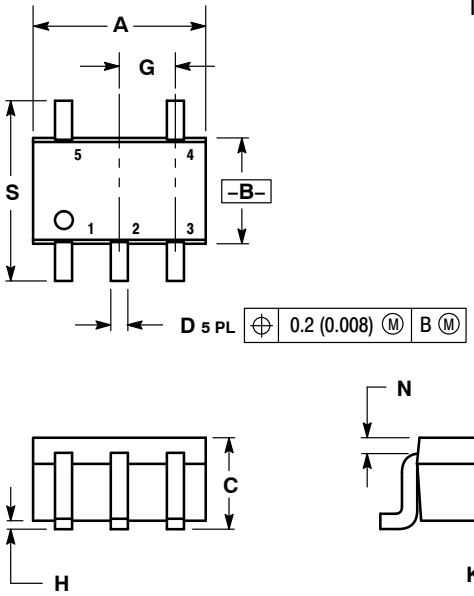
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable.

Pin 1 Orientation in Tape and Reel



PACKAGE DIMENSIONS

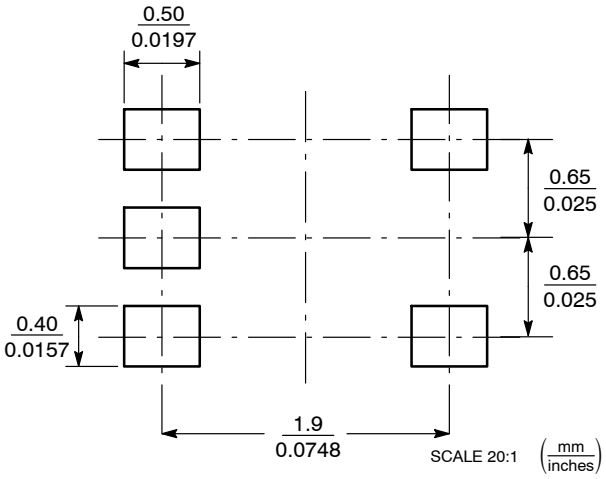
SC−88A (SC−70−5/SOT−353)
CASE 419A−02
ISSUE L



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419A−01 OBSOLETE. NEW STANDARD 419A−02.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

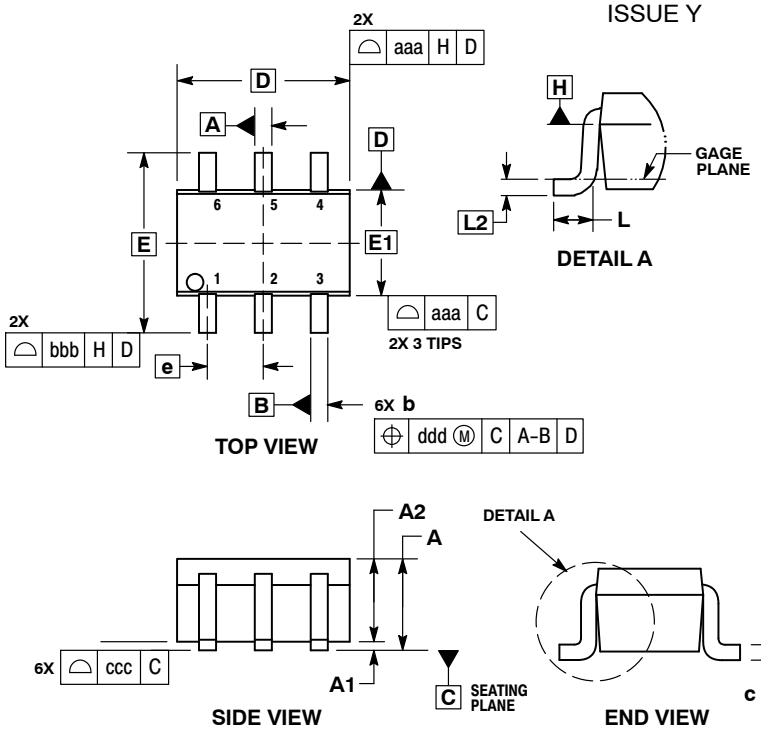
	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

SOLDER FOOTPRINT



PACKAGE DIMENSIONS

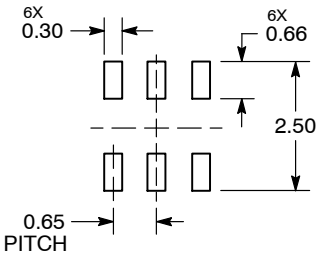
SC−88/SC70−6/SOT−363
CASE 419B−02
ISSUE Y



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	0.043
A1	0.00	---	0.10	0.000	---	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10			0.004		

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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